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~~accordance with an applied voltage between said pixel electrode and said counter electrode; and  
a drive circuit constituted by ferroelectric gate field-effect transistors respectively  
connected to said pixel electrodes, wherein said drive circuit writes data to said ferroelectric gate  
field-effect transistors in order of a row.~~

~~Claim 3,~~ line 2, delete "1 or".

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Claim 4 (Amended). ~~[The] A two-dimensional active-matrix type light modulation~~  
device [as set forth in any one of claims 1 through 3] comprising:  
a plurality of pixel electrodes arranged in the form of a two-dimensional matrix  
consisting of rows and columns;  
a plurality of counter electrodes;  
a plurality of light modulating layers, each light modulating layer being interposed  
between said pixel electrode and said counter electrode for modulating light incident thereon in  
accordance with an applied voltage between said pixel electrode and said counter electrode; and  
a drive circuit constituted by ferroelectric gate field-effect transistors respectively  
connected to said pixel electrodes, wherein said drive circuit changes a ferroelectric gate of said  
ferroelectric gate field-effect transistor to a first polarization state and then writes data in  
accordance with input of data [so that], changing said first polarization state [is changed] to a  
second polarization state, or [so that] said first polarization state [is held], in accordance with  
said input of data.

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~~Claim 5 (Amended). [The] A two-dimensional active-matrix type light modulation~~

device [as set forth in any of claims 1 through 4] comprising:

a plurality of pixel electrodes arranged in the form of a two-dimensional matrix  
consisting of rows and columns;

a plurality of counter electrodes;

a plurality of light modulating layers, each light modulating layer being interposed  
between said pixel electrode and said counter electrode for modulating light incident thereon in  
accordance with an applied voltage between said pixel electrode and said counter electrode; and

a drive circuit constituted by ferroelectric gate field-effect transistors respectively  
connected to said pixel electrodes, wherein said drive circuit performs row selection with a gate  
electrode of said ferroelectric gate field-effect transistor and writes data with a source electrode  
and drain electrode of said ferroelectric gate field-effect transistor and a substrate electrode or  
back-surface electrode of said ferroelectric gate field-effect transistor.

Claim 6 (Amended). [The] A two-dimensional active-matrix type light modulation  
device [as set forth in any of claims 1 through 5] comprising:

a plurality of pixel electrodes arranged in the form of a two-dimensional matrix  
consisting of rows and columns;

a plurality of counter electrodes;

a plurality of light modulating layers, each light modulating layer being interposed  
between said pixel electrode and said counter electrode for modulating light incident thereon in  
accordance with an applied voltage between said pixel electrode and said counter electrode; and

a drive circuit constituted by ferroelectric gate field-effect transistors respectively

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connected to said pixel electrodes wherein said drive circuit performs modulation by binary static drive.

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~~Claim 8 (Amended). A [The] two-dimensional active-matrix type light-emitting device~~  
[as set forth in claim 7] comprising:

a plurality of pixel electrodes arranged in the form of a two-dimensional matrix  
consisting of rows and columns;

a plurality of counter electrodes;

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a plurality of light-emitting layers, each light-emitting layer being interposed between  
said pixel electrode and said counter electrode for emitting light in accordance with current  
flowing through the light-emitting layer between said pixel electrode and said counter electrode;  
and

a drive circuit constituted by ferroelectric gate field-effect transistors respectively  
connected to said pixel electrodes, wherein said drive circuit writes data to said ferroelectric gate  
field-effect transistors in order of a row

Claim 9, line 2, delete "7 or".

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~~Claim 10 (Amended). A [The] two-dimensional active-matrix type light-emitting device~~  
[as set forth in any one of claims 7 through 9] comprising:

a plurality of pixel electrodes arranged in the form of a two-dimensional matrix  
consisting of rows and columns;

a plurality of counter electrodes;

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a plurality of light-emitting layers, each light-emitting layer being interposed between  
said pixel electrode and said counter electrode for emitting light in accordance with current

~~flowing through the light-emitting layer between said pixel electrode and said counter electrode;~~

and

a drive circuit constituted by ferroelectric gate field-effect transistors respectively  
connected to said pixel electrodes, wherein said drive circuit changes a ferroelectric gate of said  
ferroelectric gate field effect transistor to a first polarization state and then writes data in  
accordance with input of data [so that], changing said first polarization state [is changed] to a  
second polarization state, or [so that] said first polarization state [is held], in accordance with  
said input of data.

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Claim 11 (Amended). A [The] two-dimensional active-matrix type light-emitting device  
[as set forth in any one of claims 7 through 10] comprising:

a plurality of pixel electrodes arranged in the form of a two-dimensional matrix  
consisting of rows and columns;

a plurality of counter electrodes;

a plurality of light-emitting layers, each light-emitting layer being interposed between  
said pixel electrode and said counter electrode for emitting light in accordance with current  
flowing through the light-emitting layer between said pixel electrode and said counter electrode;

and

a drive circuit constituted by ferroelectric gate field-effect transistors respectively  
connected to said pixel electrodes, wherein said drive circuit performs row selection with a gate  
electrode of said ferroelectric gate field-effect transistor and writes data with a source electrode  
and drain electrode of said ferroelectric gate field-effect transistor and a substrate electrode or  
back-surface electrode of said ferroelectric gate field-effect transistor.

**Please add the following new claims:**

--12. The two dimensional active-matrix type light modulation device according to claim 2, wherein said drive circuit changes a ferroelectric gate of said ferroelectric gate field-effect transistor to a first polarization state and then writes data in accordance with input of data, changing said first polarization state to a second polarization state, or so said first polarization state is held in accordance with said input of data.

13. The two dimensional active-matrix type light modulation device according to claim 2 or 4, wherein said drive circuit performs row selection with a gate electrode of said ferroelectric gate field-effect transistor and writes data with a source electrode and drain electrode of said ferroelectric gate field-effect transistor and a substrate electrode or back-surface electrode of said ferroelectric gate field-effect transistor.

14. The two dimensional active-matrix type light modulation device according to any one of claims 2, 4 and 5, wherein said drive circuit performs modulation by binary static drive.

15. The two-dimensional active-matrix type light-emitting device as set forth in claim 8, wherein said drive circuit changes a ferroelectric gate of said ferroelectric gate field effect transistor to a first polarization state and then writes data in accordance with input of data, changing said first polarization state to a second polarization state, or said first polarization state is held in accordance with said input of data.

16. The two-dimensional active-matrix type light-emitting device as set forth in claim 8 or 10, wherein said drive circuit performs row selection with a gate electrode of said ferroelectric gate field-effect transistor and writes data with a source electrode and drain electrode of said

ferroelectric gate field-effect transistor and a substrate electrode or back-surface electrode of said ferroelectric gate field-effect transistor.

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17. ~~The two-dimensional active-matrix type light-emitting device as set forth in any one~~  
112, Antec.  
of claims 2-6 and 12, wherein the ferromagnetic FET comprises a single ferromagnetic FET per pixel.

18. The two-dimensional active-matrix type light-emitting device as set forth in claim 13,  
112, Antec.  
wherein the ferromagnetic FET comprises a single ferromagnetic FET per pixel.

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19. The two-dimensional active-matrix type light-emitting device as set forth in claim 14,  
112, Antec.  
wherein the ferromagnetic FET comprises a single ferromagnetic FET per pixel.

20. The two-dimensional active-matrix type light-emitting device as set forth in any one  
112, Antec.  
of claims 8-11 and 15, wherein the ferromagnetic FET comprises a single ferromagnetic FET per pixel.

21. The two-dimensional active-matrix type light-emitting device as set forth in claim 16,  
112, Antec.  
wherein the ferromagnetic FET comprises a single ferromagnetic FET per pixel.

22. The two-dimensional active-matrix type light-emitting device as set forth in any one  
112, Antec.  
of claims 2-6 and 12, wherein the ferromagnetic FET consists of a single type of semiconductor selected from one of an n-type and a p-type semiconductor.

23. The two-dimensional active-matrix type light-emitting device as set forth in claim 13,  
112, Antec.  
wherein the ferromagnetic FET consists of a single type of semiconductor selected from one of an n-type and a p-type semiconductor.

24. ~~The two-dimensional active-matrix type light-emitting device as set forth in claim 14,~~  
<sup>112, Antec.</sup>  
wherein the ferromagnetic FET consists of a single type of semiconductor selected from one of  
an n-type and a p-type semiconductor.

25. The two-dimensional active-matrix type light-emitting device as set forth in any one  
of claims 8-11 and 15, wherein <sup>112, Antec.</sup> the ferromagnetic FET consists of a single type of semiconductor  
selected from one of an n-type and a p-type semiconductor.

26. The two-dimensional active-matrix type light-emitting device as set forth in claim 16,  
wherein <sup>112, Antec.</sup> the ferromagnetic FET consists of a single type of semiconductor selected from one of  
an n-type and a p-type semiconductor.

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31 ~~27.~~ A two-dimensional active-matrix type light modulation device comprising:  
a plurality of pixel electrodes arranged in the form of a two-dimensional matrix  
consisting of rows and columns;  
a plurality of counter electrodes;  
a plurality of light modulating layers, each light modulating layer being interposed  
between said pixel electrode and said counter electrode for modulating light incident thereon in  
accordance with an applied voltage between said pixel electrode and said counter electrode; and  
a drive circuit constituted by ferroelectric gate field-effect transistors respectively  
connected to said pixel electrodes, wherein a gate of the ferroelectric field effect transistor is  
directly connected to line selecting one of said rows.--